

SFF250/61

14849 Firestone Boulevard · La Mirada, CA 90638
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

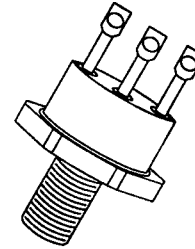
Designer's Data Sheet

FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed power package
- TX, TXV and Space Level screening available
- Replaces: IRF250 Types

**30 AMP
 200 VOLTS
 0.085 Ω
 N-CHANNEL
 POWER MOSFET**

TO-61



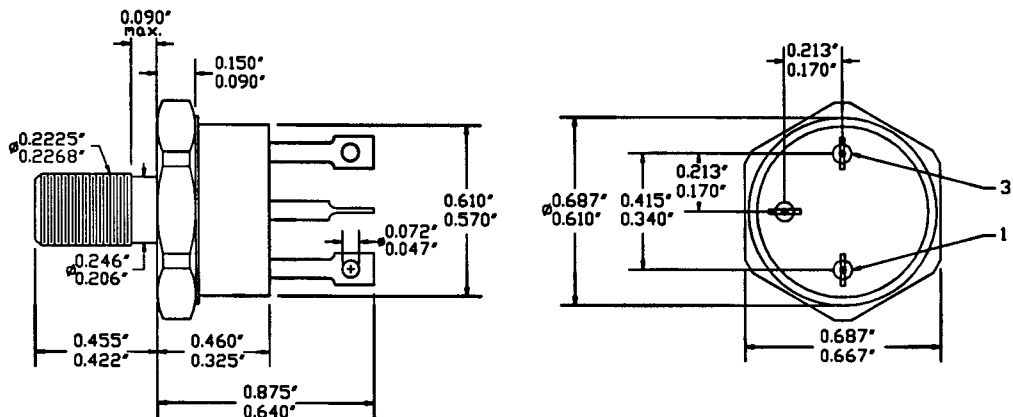
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	200	Volts
Gate to Source Voltage	V _{GS}	± 20	Volts
Continuous Drain Current	I _D	30	Amps
Operating and Storage Temperature	T _{OP} & T _{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	4	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	125 95	Watts

PACKAGE OUTLINE: TO-61

PIN OUT:

**PIN 1: SOURCE
 PIN 2: GATE
 PIN 3: DRAIN**



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F0055 B

MED

SFF250/61

PRELIMINARY



SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

ELECTRICAL CHARACTERISTICS @ T_J=25° C (Unless Otherwise Specified):

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250μA)		BV _{DSS}	200	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=60% Rated ID)		R _{DS(on)}	---	0.08	0.085	Ω
On State Drain Current (VDS > ID(on) X RDS(on) Max, VGS=10 V)		ID(on)	30	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250μA)		VGS(th)	2	3	4	V
Forward Transconductance (VDS > ID(on) X RDS(on) Max, ID=60% rated ID)		g _{fs}	13	15	---	S(Ω)
Zero Gate Voltage Drain Current (VDS=80% rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125° C)		IDSS	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated VGS	IGSS	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	VGS=10 Volts 50% rated VDS Rated ID	Q _g Q _{gs} Q _{gd}	---	80 12 44	120 20 65	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	VDD=50% rated VDS 50% rated ID RG= 6.2 Ω	t _{d(on)} t _r t _{d(off)} t _f	---	20 120 70 80	30 180 100 120	nsec
Diode Forward Voltage (IS=rated ID, VGS=0 V, T _J =25° C)		VSD	---	1.1	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25° C IF=10A di/dt=100 A/μsec	t _{rr} QRR	140 1.8	300 3.8	630 8	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	VGS=0 Volts VDS=25 Volts f= 1 MHz	C _{iss} C _{oss} C _{rss}	---	2600 650 150	---	pF

SAFE OPERATING AREA (S.O.A.)
 TC = 25 C, D.C. CONDITION

